

# isc N-Channel MOSFET Transistor

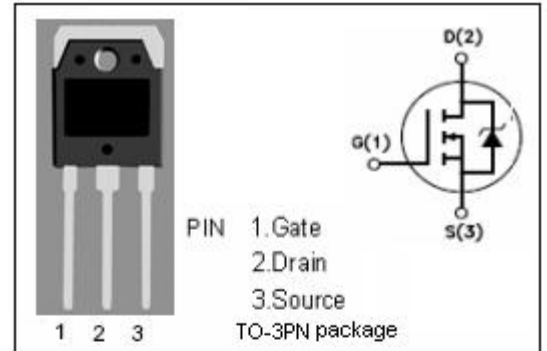
## 2SK2024-01

### DESCRIPTION

- Drain Current  $-I_D = 3A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 600V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

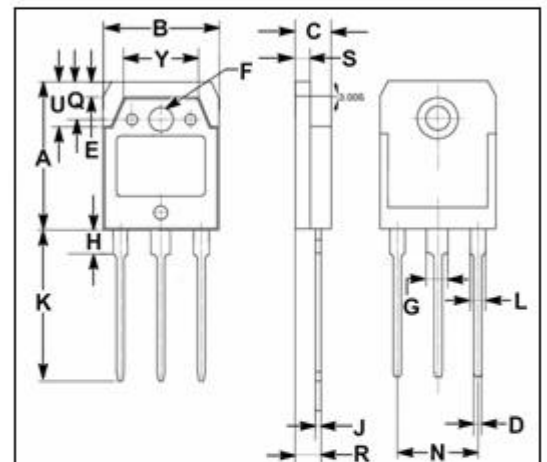
### APPLICATIONS

- Switching regulator
- UPS
- DC-DC converters
- General purpose power amplifier



### ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_C = 25^\circ C$	3	A
$I_{D(\text{puls})}$	Pulsed Drain Current	12	A
$P_{\text{tot}}$	Total Dissipation@ $T_C = 25^\circ C$	50	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{\text{stg}}$	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	35	$^\circ C/W$

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• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.5	3.0	3.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 1.5A		4.0	4.5	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0		10	500	μA
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V;		600	900	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>GS</sub> =0V; f <sub>r</sub> =1MHz		10	15	
C <sub>oss</sub>	Output Capacitance			50	75	
t <sub>r</sub>	Rise Time	V <sub>GS</sub> =10V;		10	15	ns
t <sub>d(on)</sub>	Turn-on Delay Time	I <sub>D</sub> =3A;		15	25	
t <sub>f</sub>	Fall Time	V <sub>DD</sub> =300V; R <sub>L</sub> =10 Ω		10	15	
t <sub>d(off)</sub>	Turn-off Delay Time			40	60	

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